

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L7	0	365/023	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:11
L8	8592	((365/203) or (365/204) or (365/205) or (365/206) or (365/207) or (365/208) or (327/560) or (327/561) or (327/562) or (327/563) or (257/288) or (257/e29.195)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:14
L9	13	L8 and (signal sense) near1 (amplifying amplifier amplification) and (varact?r variable adj capacitor gated adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:15
L10	15	L8 and (signal sense) near1 (amplifying amplifier amplification) and (varact?r variable adj capacitor gated adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 12:15
S1	3	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:22
S2	13	millier near2 compensating adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 14:41
S3	4	"751713".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 14:44
S4	0	gated adj diode and (nonlinear variable) near3 "capacitance."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:45
S5	7	gated adj diode and (nonlinear variable) near3 capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 14:46

S6	2	gated adj diode and (nonlinear variable) near3 capacitance and (applifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:16
S7	6	gated adj diode and (nonlinear variable vary) near3 capacitance and (applifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:20
S8	6	gated adj diode and (nonlinear variable vary) near3 capacitance and (applifying amplification amplifier amplify)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:27
S9	3	gated adj diode near4 amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:50
S10	33	small adj signal adj sensing and dram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:52
S11	0	fated adj diode.ti,ab,clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:52
S12	83	gated adj diode.ti,ab,clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 15:54
S13	31	gated adj diode.ti. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:03
S14	148	(257/312).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:11
S15	4	MOSFET near5 body adj bias.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 16:15

S16	100	flash adj memory adj cell adj array and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/09 16:45
S17	24	flash adj memory adj cell adj array.ti,ab,clm. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/09 16:45
S18	4	"751714".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:09
S19	1	(US-20050145895-\$).did.	US-PGPUB	OR	OFF	2005/08/26 07:09
S20	4	"571713".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:10
S21	5	"751713".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:10
S22	1	(US-20050146928-\$).did.	US-PGPUB	OR	OFF	2005/08/26 07:11
S23	175	variable near2 (capacitor capacitance) and sense adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 07:12
S24	398	(varying varies vary variable) near2 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:15
S25	296	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:29
S26	258	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and (gate control adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:29

S27	255	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:32
S28	183	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:34
S29	143	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:36
S30	60	(varying varies vary variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance) same ("well" "n-well" "p-well" nwell pwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:37
S31	25	(variable) near1 (capacitor capacitance) and sense adj amplifier and semiconductor and circuit and gate and (MOSFET FET field adj effect adj transistor MISFET MOS adj transistor MIS adj transistor) same (capacitor capacitance) same ("well" "n-well" "p-well" nwell pwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 07:38
S32	10	(US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$ or US-20050104119-\$ or US-20050104118-\$ or US-20050099859-\$ or US-20030206437-\$).did. or (US-6731529-\$ or US-6418044-\$ or US-6414862-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/26 07:42
S33	13	diorio.in. and variable adj capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:20

S34	10	(US-20030206437-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-6414862-\$ or US-6418044-\$ or US-6731529-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/26 08:34
S35	2	("6144581").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:36
S36	0	("gatedadjdiodeandvariableadj(capacitancecapacitor)and(MOSadjtransistorMOSFETFETMISadjtransistorMISFET)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:37
S37	2	gated adj diode and variable adj (capacitance capacitor) and (MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:43
S38	3	gated adj diode and (varactor variable adj (capacitance capacitor)) and (MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:44
S39	3	gated adj diode and (varactor variable adj (capacitance capacitor)) and (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:44
S40	3	gated near1 diode and (varactor variable adj (capacitance capacitor)) and (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46
S41	846	(varactor variable adj (capacitance capacitor)) near10 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46
S42	536	(varactor variable adj (capacitance capacitor)) near4 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:46

S43	11	(varactor variable adj (capacitance capacitor)) near4 (field adj effect adj transistor MOS adj transistor MOSFET FET MIS adj transistor MISFET) and sense adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 08:57
S44	1942	((365/207) or (365/208)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:57
S45	1609	S44 and sense adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:58
S46	0	S44 and sense adj amplifier and gated adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 08:58
S47	6	S44 and sense adj amplifier and (varactor capacitor near4 variable)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:07
S48	2	("5844265").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:54
S49	57	gated adj diode near6 ("well" "n-well" "p-well" pwell nwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 09:55
S50	52	gated adj diode near4 ("well" "n-well" "p-well" pwell nwell)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:09
S51	2	("6674116").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:10
S52	1	S51 and "well"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 10:10

S53	0	("well" nwell pwell) near4 gated adj diode near10 vary near2 capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 10:12
S54	10	("well" nwell pwell) near4 (varactor gated adj diode) near10 vary near2 capacitance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:09
S55	108	cascade near4 protect\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:10
S56	935	cascade.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:10
S57	8	cascade.ti. and protect\$3.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:11
S58	8	cascade.ti. and protect\$3.ti. and cascade	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 11:11
S59	1	"5844265".pn. and (threshold protect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 13:37
S60	10	"sample/hold" near4 latch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 16:20
S61	15	(US-20030206437-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-5838176-\$ or US-5844265-\$ or US-6097432-\$ or US-6414862-\$ or US-6418044-\$ or US-6674116-\$ or US-6731529-\$ or US-6794707-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/26 16:33

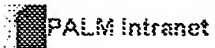
S62	9	S61 and overlap\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/26 16:37
S63	2	gated adj diode near4 (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:38
S64	10	mos adj capacitor near4 (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:40
S65	10	mos adj capacitor near4 (overlap overlapping) and (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:44
S66	21	mos adj capacitor.ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:48
S67	27	(gate adj diode mos adj capacitor).ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:49
S68	6	(gate adj diode).ti.ab. and gate near4 (overlap overlapping) and (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/26 16:49
S69	74	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:31
S70	18	(gated adj diode) and sense adj amplifier and invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:14
S71	34	(varactor) and sense adj amplifier and invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:15

S72	25	(variable adj capacitor) and sense adj amplifier and invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:15
S73	10	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert?r and control adj line and signal adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:31
S74	9	(gated adj diode varactor variable adj capacitor) and sense adj amplifier and invert?r and control adj line and signal adj line and (opamp difference differential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:42
S75	24	(gated adj diode MOS adj capacitor MIS adj capacitor) and sense adj amplifier and invert?r and control adj line and signal adj line and (opamp difference differential)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:48
S76	24	(gated adj diode MOS adj capacitor MIS adj capacitor) and sense adj amplifier and invert?r and control adj line and signal adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/27 15:48
S77	0	gated adj diode.clm. and sense adj amplifier.clm. and signal adj line and control adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23
S78	1	gated adj diode.clm. and (signal sense) adj amplifier.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23
S79	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 15:23
S80	2	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:25
S81	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying).clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26

S82	1	gated adj diode.clm. and (signal sense) adj (amplification amplifier amplifying).ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26
S83	1	gated adj diode.ti,ab,clm. and (signal sense) adj (amplification amplifier amplifying).ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:26
S84	3	gated adj diode.ti,ab,clm. and (signal sense) adj (amplification amplifier amplifying).ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:28
S85	1	gated adj diode.ti,ab,clm. and (signal sense) adj amplifier.ti,ab,clm. and gated adj diode and (sense signal) adj (amplifying amplification amplifier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:30
S86	3	gated adj diode near20 (signal sense) adj amplifier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:31
S87	19	(US-20030123276-\$ or US-20030206437-\$ or US-20040136251-\$ or US-20050099859-\$ or US-20050104118-\$ or US-20050104119-\$ or US-20050145895-\$ or US-20050146928-\$ or US-20050184787-\$).did. or (US-4538287-\$ or US-5838176-\$ or US-5844265-\$ or US-6097432-\$ or US-6414862-\$ or US-6418044-\$ or US-6674116-\$ or US-6687175-\$ or US-6731529-\$ or US-6794707-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/08/28 15:56
S88	49076	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm.	US-PGPUB; USPAT	OR	ON	2005/08/28 15:56
S89	120366	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:04

S90	15582	(gated adj diode varactor variable adj (capacitance capacitor)).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:57
S91	618	S89 and S90	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:02
S92	572	S91 and @ad<"20040106"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:59
S93	133	S91 and @ad<"20040106" and (invert?r latch buffer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 15:59
S94	353	S89 and S90	USPAT	OR	ON	2005/08/28 16:02
S95	4	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and (gated adj diode).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:05
S96	4	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and (gated adj diode).ti,ab,clm. and gated adj diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:06
S97	17	(amplifier amplification amplifying) near2 (signal sense).ti,ab,clm. and gated adj diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:10
S98	1	bridge adj demodulat?r adj amplifier and gated adj diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:13

S99	721	(variable adj capacitor varactor varacter) and (inverter inverter latch buffer) and (signal sense) adj (amplifier amplification)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:24
S100	721	(variable adj capacitor varactor varacter) and (inverter inverter latch buffer) and ((signal sense) adj (amplifier amplification) amplifying near2 signal) and (signal sense) adj (amplification amplifier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:49
S101	920	((327/560) or (327/561) or (327/562) or (327/563)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/28 16:49
S102	18	S101 and (varact?r variable adj (capacitor capacitance) gated adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 16:50
S103	33	(gated adj diode varact?r) near5 (overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 09:35
S104	47	(gated adj diode varact?r variable adj capacitor).ti,ab,clm. and (overlap overlapping) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 09:35
S105	41	(gated adj diode varact?r variable adj capacitor).ti,ab,clm. and (overlap overlapping) near6 gate not S103	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 09:35



Application Number

IDS Flag Clearance for Application

**IDS
Information**

Content	Mailroom Date	Entry Number	IDS Review	Reviewer
M844	01-05-2004	11	<input checked="" type="checkbox"/>	08-11-2005 00:53:04 IDS CONV